IN THE CLAIMS

Please amend the claims as follows.

1-44. (Canceled).

45. (Previously Presented) A method of providing a material in a site between metal features on a wafer, comprising:

performing a deposition of said material over said wafer in said site, wherein said deposition occurs at a greater rate within said site than above said features; and

etching said material in the same general site used to perform said deposition, wherein said step of etching further comprises etching generally simultaneously with performing said deposition.

46. (Previously Presented) A method of providing a material in a site between metal features on a wafer, comprising:

performing a deposition of said material in said site, wherein said step of performing a deposition further comprises depositing a polymer on said wafer, wherein said deposition occurs at a greater rate within said site than above said features; and

etching said material in the same general site used to perform said deposition, wherein said step of etching further comprises etching generally simultaneously with performing said deposition.

47. (Previously Presented) The method in claim 45, wherein said deposition occurs above said features.

48. (Currently Amended) A method of providing a material in a site between metal features on a wafer, comprising:

performing a deposition of said material in said site; and

plasma etching ~~said material and~~ a conductive material in the same general site used to perform said deposition,

wherein said plasma etching further comprises etching generally simultaneously with performing said deposition.

49. (Previously Presented) The method in claim 48, wherein said step of performing a deposition comprises performing a plasma deposition.

50. (Previously Presented) The method of claim 49, wherein plasma etching includes plasma etching a horizontal portion of the material on a surface of the wafer adjacent the site.

51. (Previously Presented) The method of claim 48, wherein plasma etching includes plasma etching a horizontal portion of the material on a surface of the wafer adjacent the site.

52. (Previously Presented) The method of claim 48, wherein plasma etching further includes preventing deposition of the material outside the site.

53. (Previously Presented) The method of claim 48, wherein plasma etching further includes flowing CF_4 at a rate of 25 sccm/minute to 200 sccm/minute.

54. (Previously Presented) The method of claim 45, wherein performing a deposition includes depositing within said site a layer of deposited material having a thickness of 50 angstroms or greater.

55. (Previously Presented) The method of claim 45, wherein etching said material in the same general site used to perform said deposition includes etching a conductive layer from a surface of the wafer.

56. (Previously Presented) The method of claim 45, wherein etching said material prevents said material from forming on the metal features.

57. (Previously Presented) The method of claim 46, wherein etching said material prevents said polymer from forming on the metal features.

58. (Previously Presented) The method of claim 48, wherein said deposition occurs at a greater rate within said site than above said features